
PRINCIPLES OF CMOS VLSI DESIGN

A Systems Perspective

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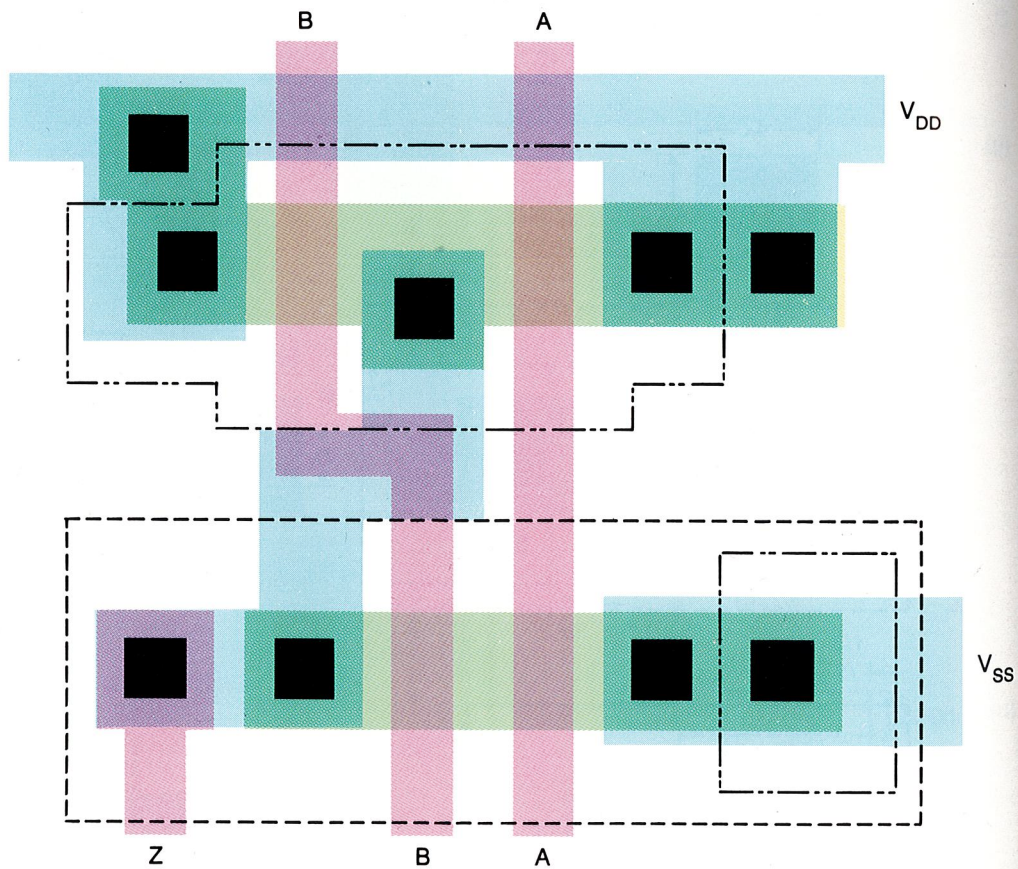
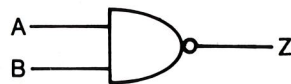
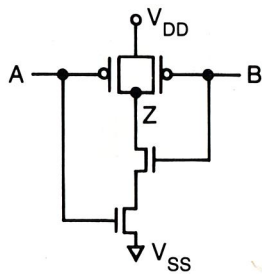
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